

3SK300

Silicon N Channel Dual Gate MOS FET
UHF / VHF RF Amplifier

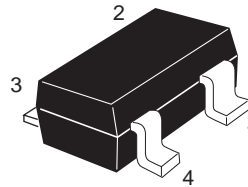
REJ03G0818-0300
(Previous ADE-208-449A)
Rev.3.00
Aug.10.2005

Features

- Low noise figure.
NF = 1.0 dB typ. at f = 200 MHz
- High gain
PG = 27.6 dB typ. at f = 200 MHz

Outline

RENESAS Package code: PLSP0004ZA-A
(Package name: MPAK-4)



1. Source
2. Gate1
3. Gate2
4. Drain

Note: Marking is "ZR-"

Absolute Maximum Ratings

(Ta = 25°C)

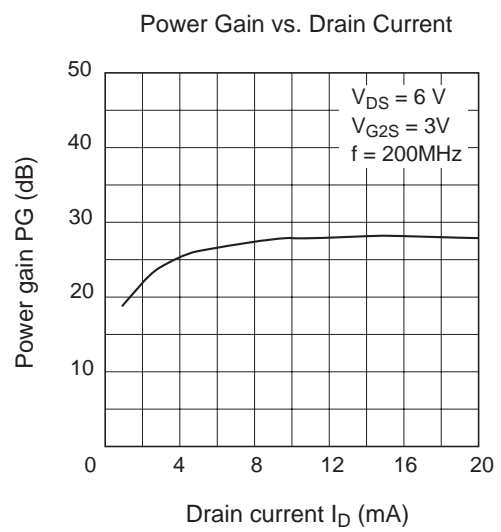
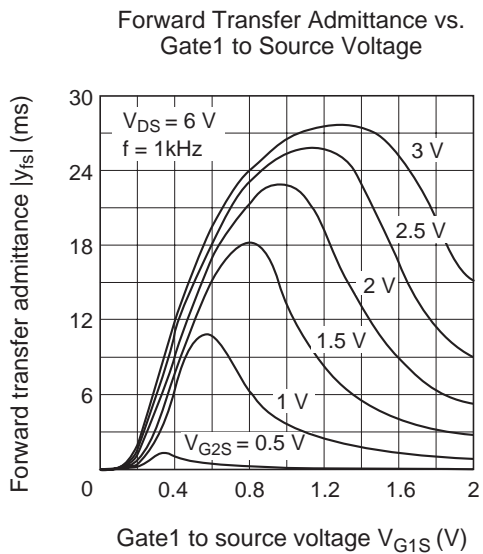
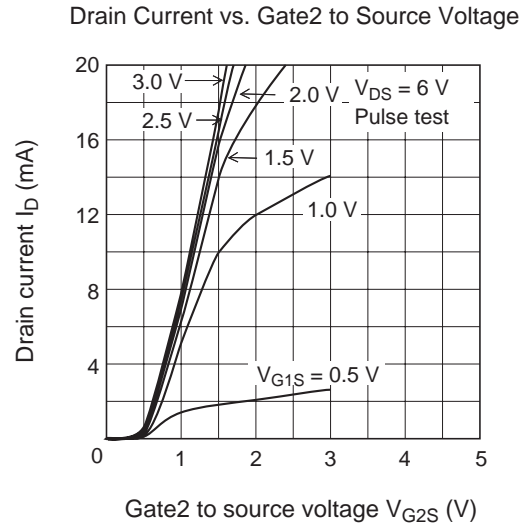
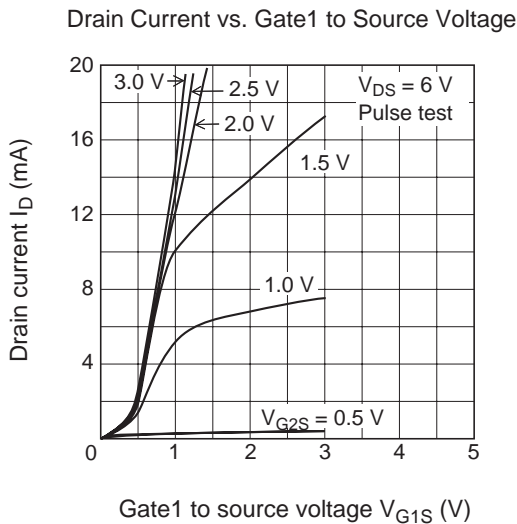
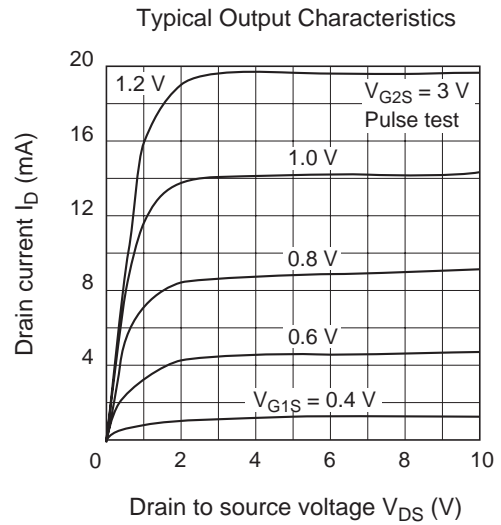
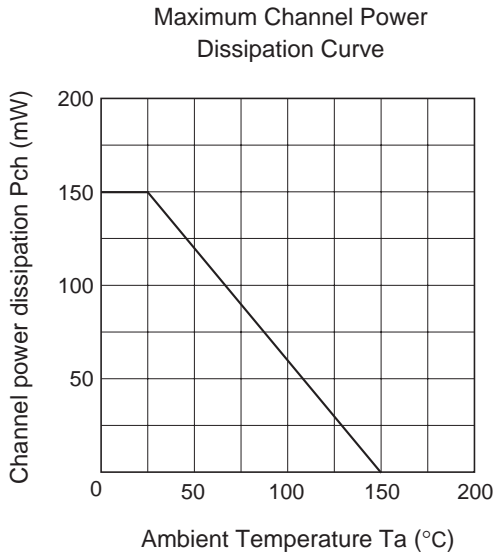
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DS}	14	V
Gate 1 to source voltage	V_{G1S}	± 8	V
Gate 2 to source voltage	V_{G2S}	± 8	V
Drain current	I_D	25	mA
Channel power dissipation	Pch	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics

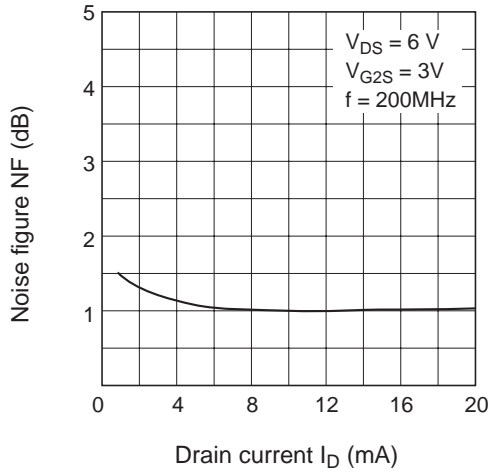
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSX}$	14	—	—	V	$I_D = 200 \mu A$, $V_{G1S} = -3 V$, $V_{G2S} = -3 V$
Gate 1 to source breakdown voltage	$V_{(BR)G1SS}$	± 8	—	—	V	$I_{G1} = \pm 10 \mu A$, $V_{DS} = V_{G2S} = 0$
Gate 2 to source breakdown voltage	$V_{(BR)G2SS}$	± 8	—	—	V	$I_{G2} = \pm 10 \mu A$, $V_{DS} = V_{G1S} = 0$
Gate 1 cutoff current	I_{G1SS}	—	—	± 100	nA	$V_{G1S} = \pm 6 V$, $V_{DS} = V_{G2S} = 0$
Gate 2 cutoff current	I_{G2SS}	—	—	± 100	nA	$V_{G2S} = \pm 6 V$, $V_{DS} = V_{G1S} = 0$
Drain current	$I_{DS(op)}$	4	8	14	mA	$V_{DS} = 6 V$, $V_{G1S} = 0.75 V$, $V_{G2S} = 3 V$
Gate 1 to source cutoff voltage	$V_{G1S(off)}$	0	+0.2	+1.0	V	$V_{DS} = 10 V$, $V_{G2S} = 3 V$, $I_D = 100 \mu A$
Gate 2 to source cutoff voltage	$V_{G2S(off)}$	0	+0.3	+1.0	V	$V_{DS} = 10 V$, $V_{G1S} = 3 V$, $I_D = 100 \mu A$
Forward transfer admittance	$ y_{fs} $	20	25	—	ms	$V_{DS} = 6 V$, $V_{G2S} = 3 V$, $I_D = 10 mA$, $f = 1 kHz$
Input capacitance	C_{iss}	2.4	3.1	3.5	pF	$V_{DS} = 6 V$, $V_{G2S} = 3 V$, $I_D = 10 mA$, $f = 1 MHz$
Output capacitance	C_{oss}	0.8	1.1	1.4	pF	
Reverse transfer capacitance	C_{rss}	—	0.021	0.04	pF	
Power gain	PG	24	27.6	—	dB	$V_{DS} = 6 V$, $V_{G2S} = 3 V$, $I_D = 10 mA$, $f = 200 MHz$
Noise figure	NF	—	1.0	1.5	dB	$V_{DS} = 6 V$, $V_{G2S} = 3 V$, $I_D = 10 mA$, $f = 900 MHz$
Power gain	PG	12	15.6	—	dB	
Noise figure	NF	—	3.0	4.0	dB	$V_{DS} = 6 V$, $V_{G2S} = 3 V$, $I_D = 10 mA$, $f = 60 MHz$
Noise figure	NF	—	2.7	3.5	dB	

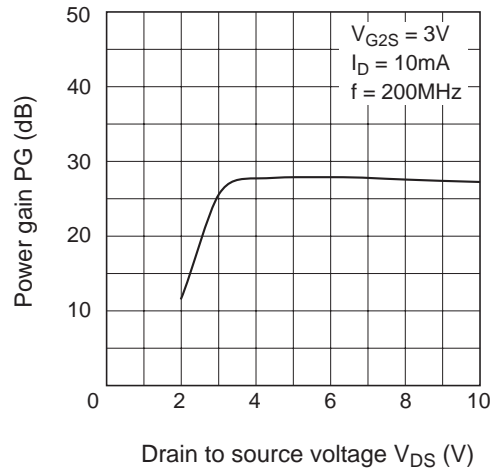
Main Characteristics



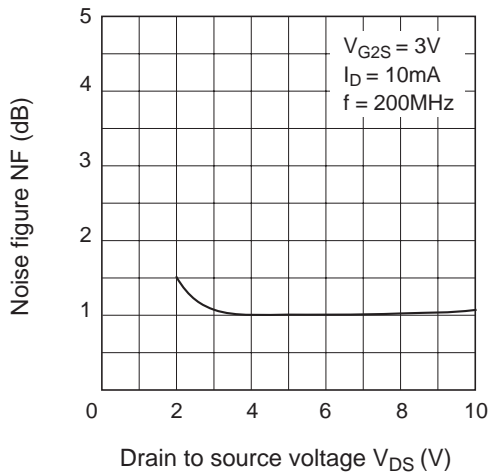
Noise Figure vs. Drain Current



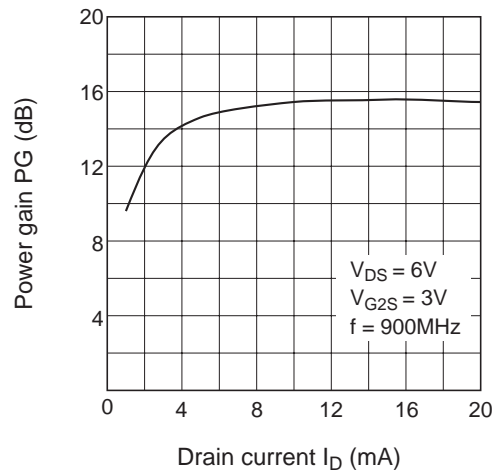
Power Gain vs. Drain to Source Voltage



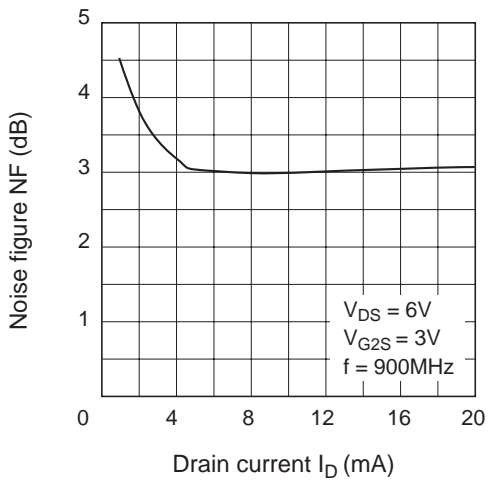
Noise Figure vs. Drain to Source Voltage



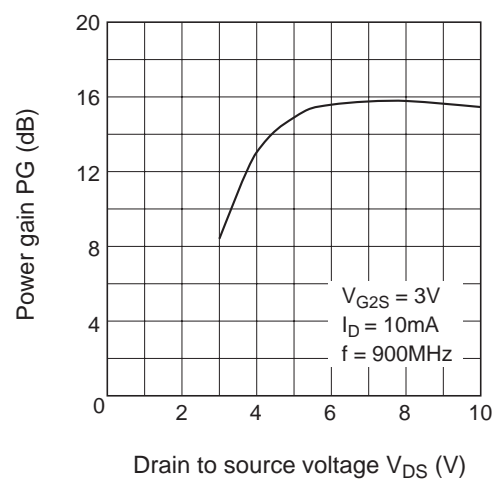
Power Gain vs. Drain Current



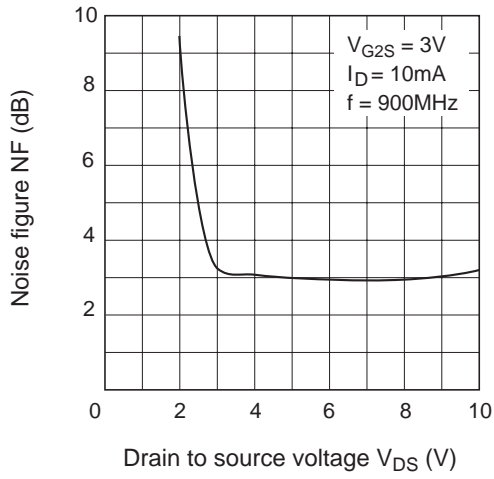
Noise Figure vs. Drain Current



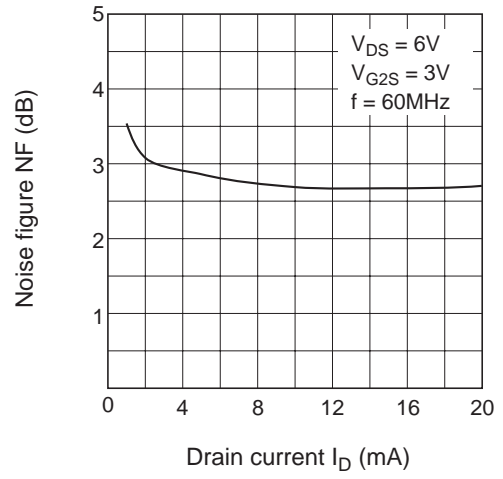
Power Gain vs. Drain to Source Voltage



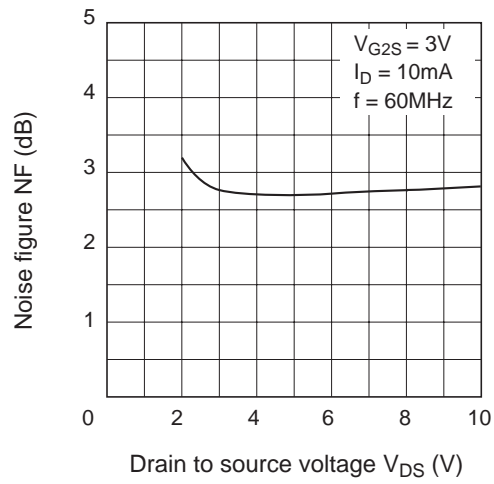
Noise Figure vs. Drain to Source Voltage



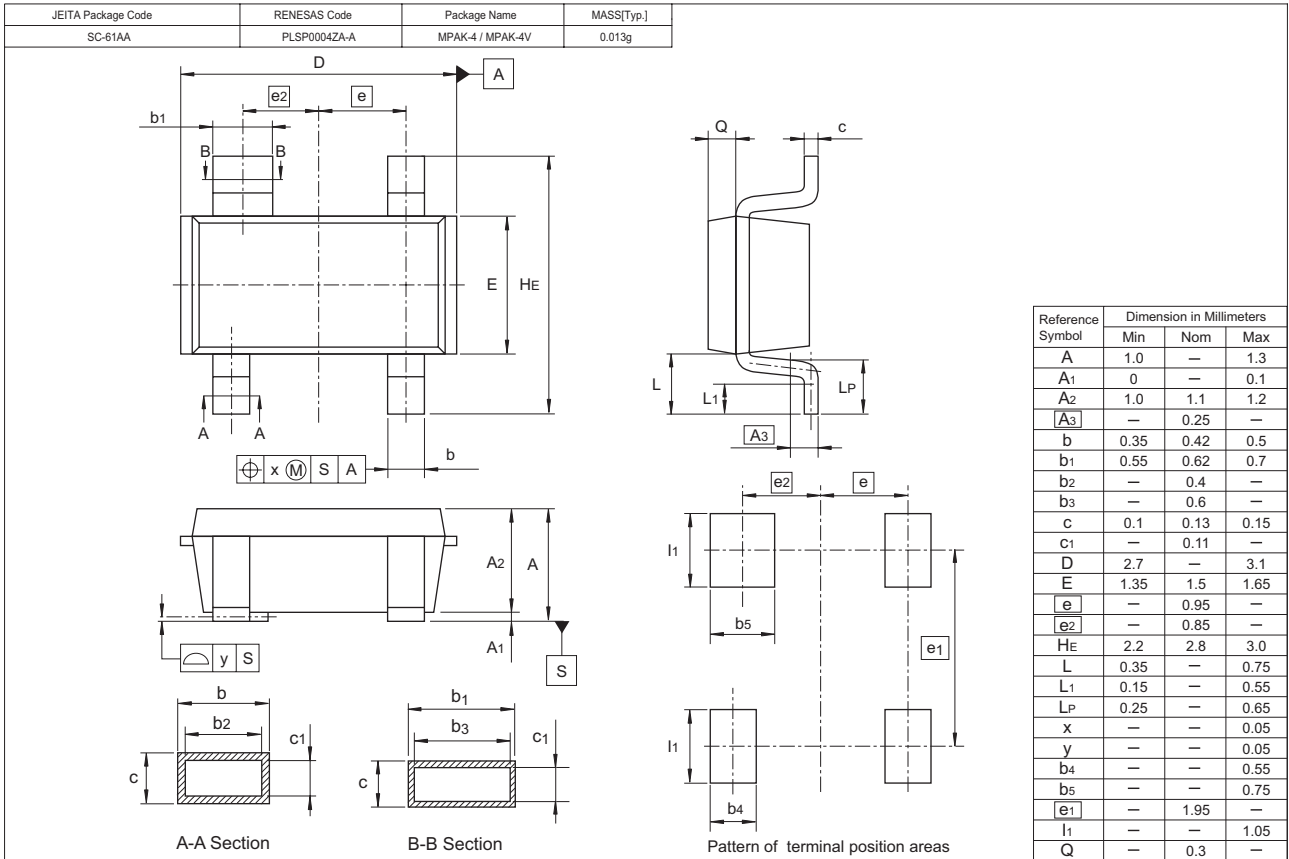
Noise Figure vs. Drain Current



Noise Figure vs. Drain to Source Voltage



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
3SK300ZR-TL-E	3000	φ 178 mm Reel, 8 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510